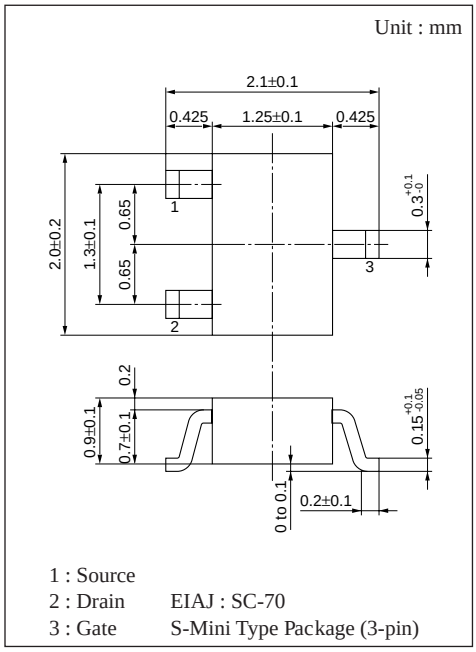
2SJ364

Silicon P-Channel Junction

For analog switch



■ Features

- Low ON-resistance
- Low-noise characteristics

■ Absolute Maximum Ratings (Ta = 25˚C)

Parameter	Symbol	Rating	Unit
Gate-Drain voltage	V_{GDS}	65	V
Drain current	I_D	– 20	mA
Gate current	I_G	–10	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	˚C
Storage temperature	T_{stg}	– 55 to +150	˚C

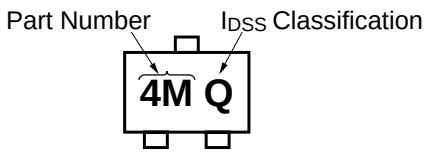
■ Electrical Characteristics (Ta = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS} *	V_{DS}= –10V, V_{GS}= 0	– 0.6		– 6	mA
Gate-Source leakage current	I_{GSS}	V_{GS}= 30V, V_{DS}= 0			10	nA
Gate-Drain voltage	V_{GDS}	I_G=10µA, V_{DS}= 0	65			V
Gate-Source cut-off voltage	V_{GSC}	V_{DS}= –10V, I_D= –10µA		1.5	3.5	V
Forward transadmittance	$\|Y_{fs}\|$	V_{DS}= –10V, I_D= –1mA, f=1kHz	1.8	2.5		mS
Drain-Source ON-resistance	$R_{DS(ON)}$	V_{DS}= –10mV, V_{GS}= 0		300		Ω
Input capacitance	C_{iss}	V_{DS}= –10V, V_{GS}= 0, f=1MHz		12		pF
Feedback capacitance	C_{rss}			4		pF

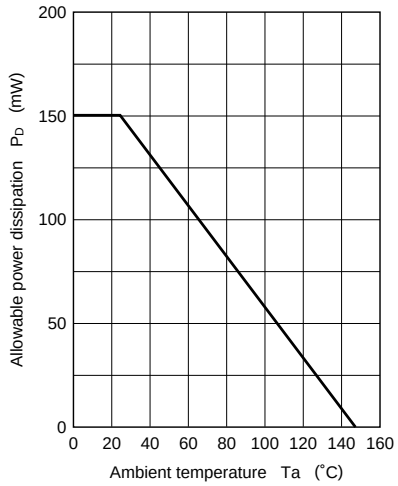
* I_{DSS} rank classification

Rank	P	Q	R
I_{DSS}(mA)	– 0.6 to –1.5	–1 to – 3	– 2.5 to –6
Part number symbol	4MP	4MQ	4MR

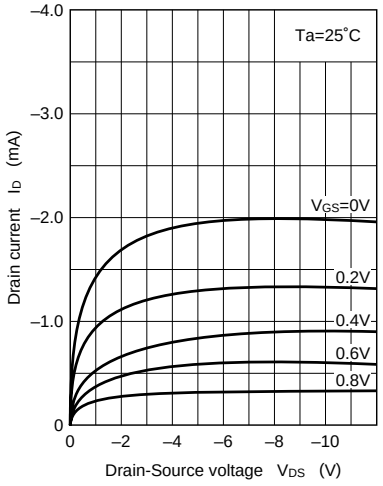
■ Marking (Example)



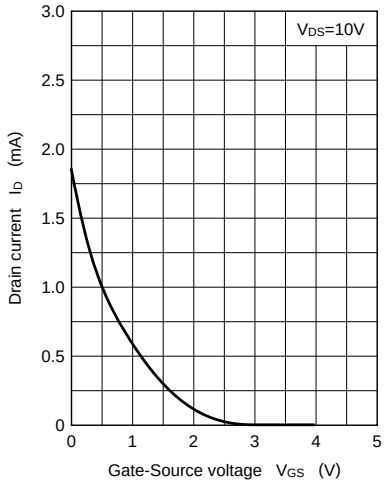
$P_D - Ta$



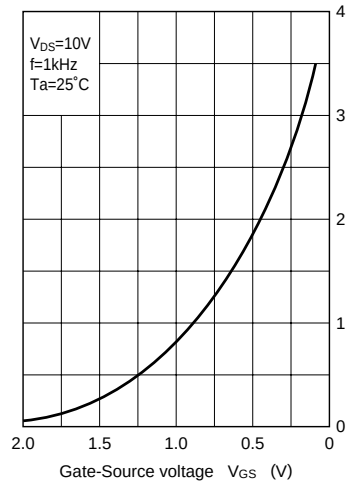
$I_D - V_{DS}$



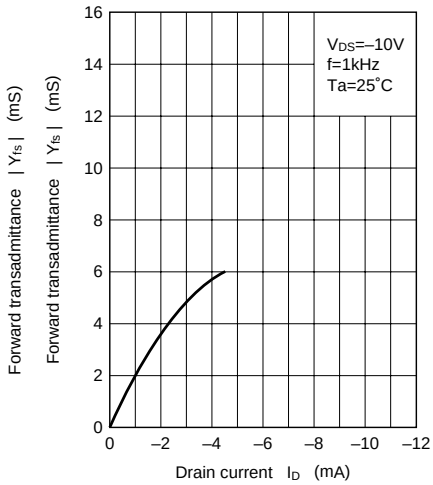
$I_D - V_{GS}$



$|Y_{fs}| - V_{GS}$



$|Y_{fs}| - I_D$



$C_{iss}, C_{oss}, C_{rss} - V_{DS}$